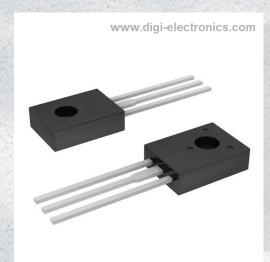


KSC2682OS Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number KSC2682OS-DG

Manufacturer onsemi

Manufacturer Product Number KSC2682OS

Description TRANS NPN 180V 0.1A TO126-3

Detailed Description Bipolar (BJT) Transistor NPN 180 V 100 mA 200MHz

1.2 W Through Hole TO-126-3



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RFQ Email: Info@DiGi-Electronics.com

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KSC2682

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
KSC2682OS	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	100 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
180 V	500mV @ 5mA, 50mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
1μA (ICBO)	100 @ 10mA, 5V
Power - Max:	Frequency - Transition:
1.2 W	200MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-225AA, TO-126-3	TO-126-3
Base Product Number:	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541 29 0075



KSC2682

Audio Frequency Power Amplifier

Complement to KSA1142



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	180	V
V _{CEO}	Collector-Emitter Voltage	180	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	100	mA
P _C	Collector Dissipation (T _a =25°C)	1.2	W
P _C	Collector Dissipation (T _C =25°C)	8	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{CBO}	Collector Cut-off Current	$V_{CB} = 180V, I_{E} = 0$			1.0	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 3V, I_{C} = 0$			1.0	μΑ
h _{FE1} h _{FE2}	* DC Current Gain	$V_{CE} = 5V, I_{C} = 1mA$ $V_{CE} = 5V, I_{C} = 10mA$	90 100	190 200	320	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = 50$ mA, $I_B = 5$ mA		0.12	0.5	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	$I_C = 50$ mA, $I_B = 5$ mA		0.8	1.5	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 20mA$		200		MHz
C _{ob}	Output Capacitance	$V_{CB} = 10V, I_{E} = 0$ f = 1MHz		3.2	5.0	pF
NF	Noise Figure	$V_{CE} = 10V$, $I_{C} = 1mA$ $R_{S} = 10K\Omega$, $f = 1kHz$		4		dB

^{*} Pulse Test: PW≤350μs, Duty Cycle≤2%

h_{FE} Classificntion

Classification	0	Y
h _{FE2}	100 ~ 200	160 ~ 320

Typical Characteristics

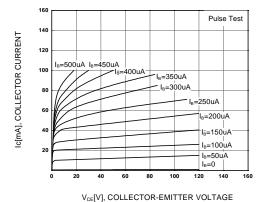


Figure 1. Static Characteristic

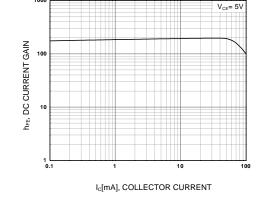


Figure 2. DC current Gain

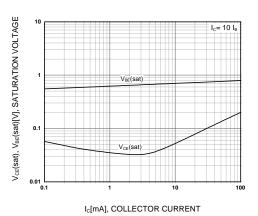


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

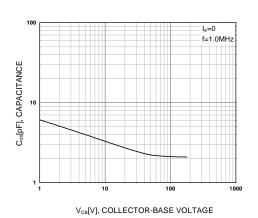


Figure 4. Collector Output Capacitance

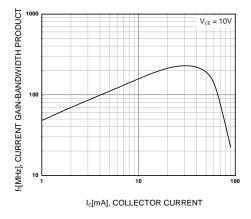


Figure 5. Current Gain Bandwidth Product

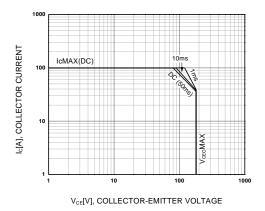
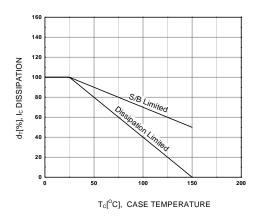


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)



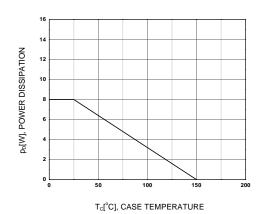
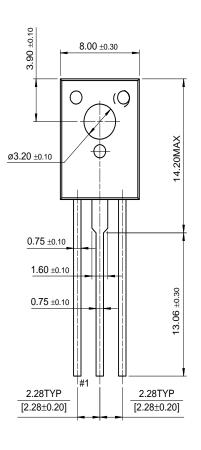


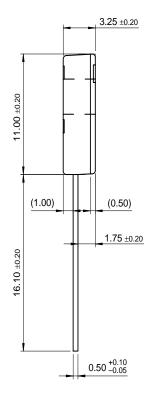
Figure 7. Derating Curve of Safe Operating Area

Figure 8. Power Derating

Package Demensions

TO-126





Dimensions in Millimeters

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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